

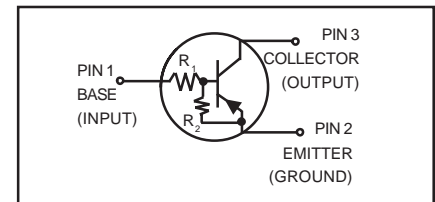
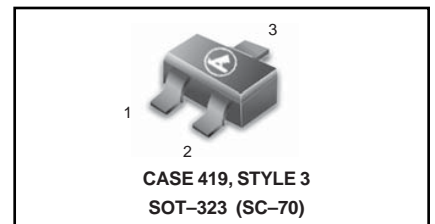
Bias Resistor Transistor

PNP Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

This digital transistors LMUN5141 is designed to replace a single device and its external resistor bias network. The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space. The device is housed in the SC-70/SOT-323 package which is designed for low power surface mount applications.

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- The SC-70/SOT-323 package can be soldered using wave or reflow. The modified gull-winged leads absorb thermal stress during soldering eliminating the possibility of damage to the die.
- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

LMUN5141T1G
S-LMUN5141T1G



ORDERING INFORMATION

Device	Marking	Shipping
LMUN5141T1G S-LMUN5141T1G	6U	3000/Tape&Reel

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current	I _c	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation	P _d	202 (Note 1)	mW
T _A = 25°C		310 (Note 2)	
Derate above 25°C		1.6 (Note 1)	°C/W
		2.5 (Note 2)	
Thermal Resistance – Junction-to-Ambient	R _{θJA}	618 (Note 1)	°C/W
Thermal Resistance – Junction-to-Lead	R _{θJL}	280 (Note 1)	°C/W
		332 (Note 2)	
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

1. FR-4 @ Minimum Pad

2. FR-4 @ 1.0 x 1.0 inch Pad

LMUN5141T1G, S-LMUM5141T1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}, I_E = 0$)	I_{CBO}	–	–	100	nAdc
Collector-Emitter Cutoff Current ($V_{CE} = 50\text{ V}, I_B = 0$)	I_{CEO}	–	–	500	nAdc
Emitter-Base Cutoff Current ($V_{BE} = 6.0\text{ V}$)	I_{EBO}	–	–	0.1	mAdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu\text{A}, I_E = 0$)	$V_{(BR)CBO}$	50	–	–	Vdc
Collector-Emitter Breakdown Voltage (Note 3) ($I_C = 2.0\text{ mA}, I_B = 0$)	$V_{(BR)CEO}$	50	–	–	Vdc

ON CHARACTERISTICS (Note 3)

DC Current Gain ($V_{CE} = 10\text{ V}, I_C = 5.0\text{ mA}$)	h_{FE}	160	350	–	
Collector-Emitter Saturation Voltage ($I_C = 10\text{ mA}, I_B = 0.3\text{ mA}$)	$V_{CE(sat)}$	–	–	0.25	Vdc
Output Voltage (on) ($V_{CC} = 5.0\text{ V}, V_B = 2.5\text{ V}, R_L = 10\text{ k}\Omega$)	V_{OL}	–	–	0.2	Vdc
Output Voltage (off) ($V_{CC} = 5.0\text{ V}, V_B = 0.5\text{ V}, R_L = 1.0\text{ k}\Omega$)	V_{OH}	4.9	–	–	Vdc
Input Resistor	R_1	70	100	130	$\text{k}\Omega$
Resistor Ratio	R_1/R_2	–	–	–	

3. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

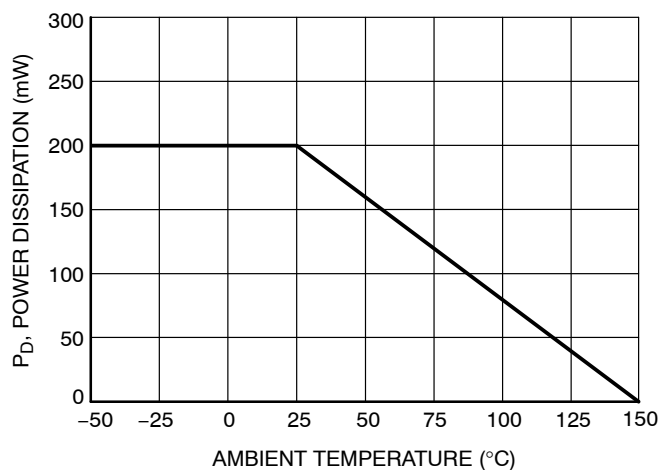


Figure 1. Derating Curve

TYPICAL ELECTRICAL CHARACTERISTICS

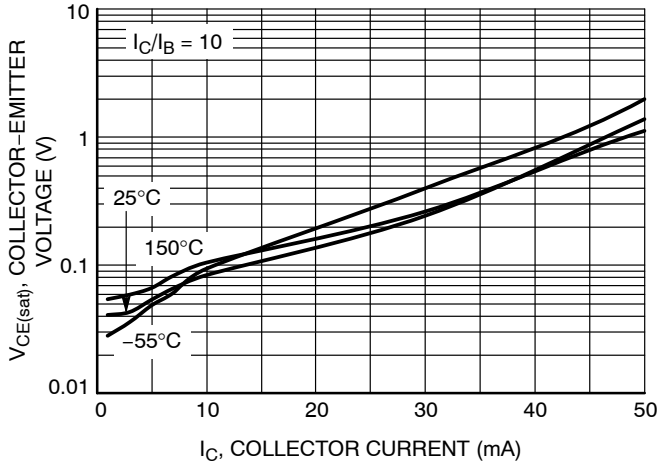


Figure 2. $V_{CE(sat)}$ vs. I_C

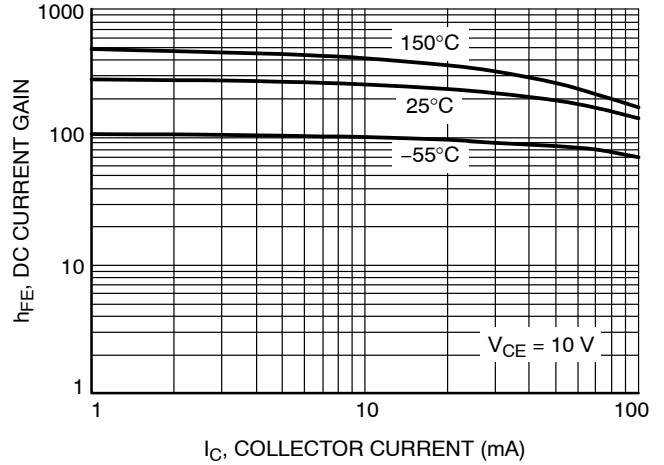


Figure 3. DC Current Gain

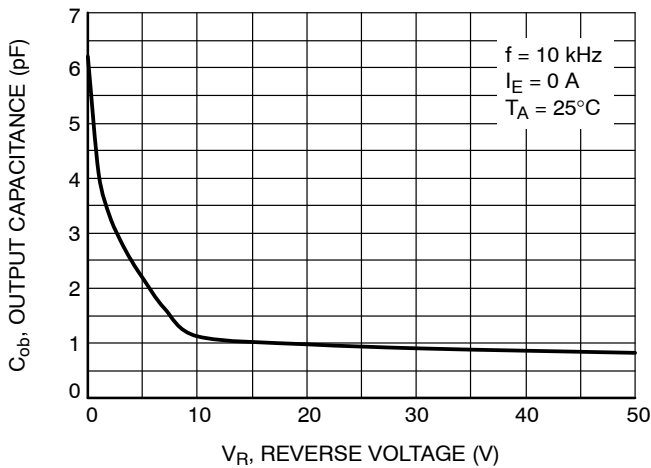


Figure 4. Output Capacitance

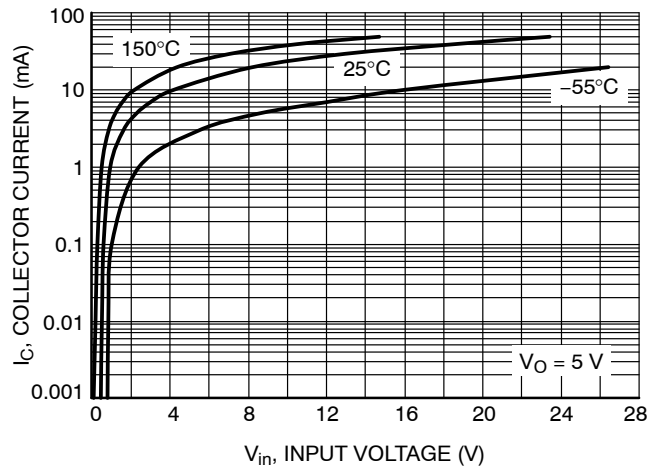


Figure 5. Output Current vs. Input Voltage

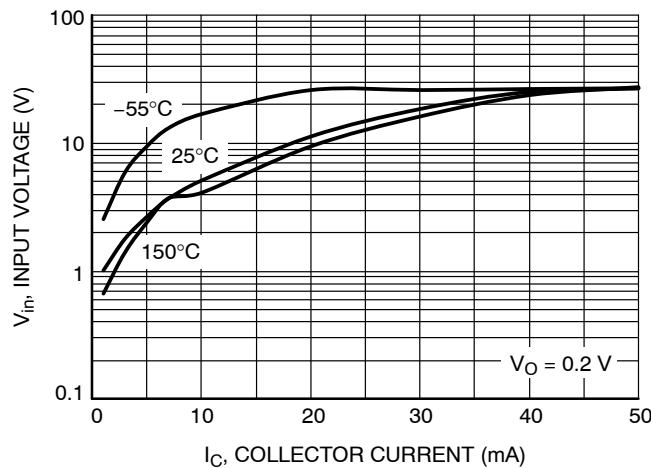
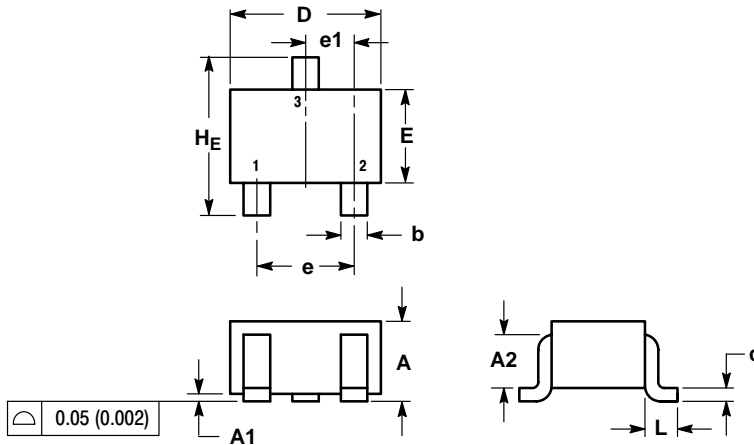


Figure 6. Input Voltage vs. Output Current

LMUN5141T1G, S-LMUM5141T1G

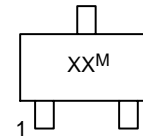
SC-70 (SOT-323)



NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.7 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.425 REF			0.017 REF		
HE	2.00	2.10	2.40	0.079	0.083	0.095

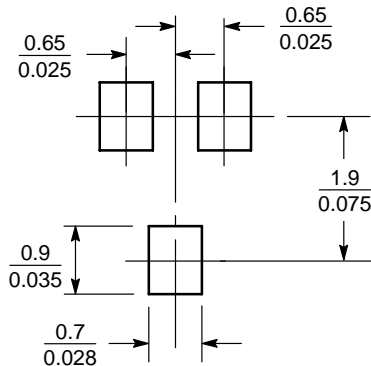
GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

SOLDERING FOOTPRINT*



SCALE 10:1 (mm/inches)

单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)